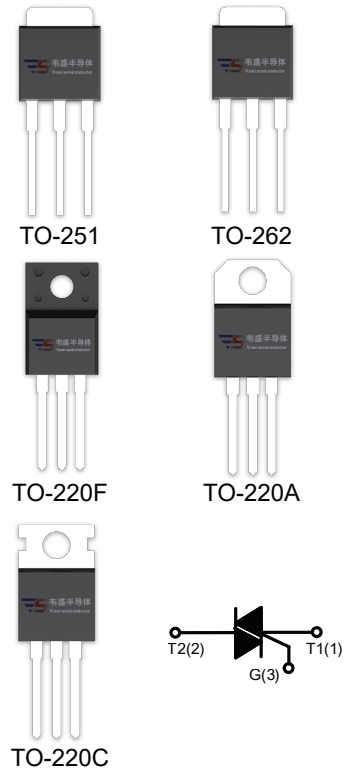


**DESCRIPTION:**

With high ability to withstand the shock loading of large current, BTB08-800TW series triacs provide high dv/dt rate with strong resistance to electromagnetic interference. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.


**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	600/800/1200	V

**ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40 - 150	°C
Operating junction temperature range		$T_j$	-40 - 125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	600/800/1200	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	600/800/1200	V
Non repetitive surge peak Off-state voltage		$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	TO-251/TO-220C TO-220A(Non-Ins) ( $T_c=100^\circ\text{C}$ )	$I_{T(RMS)}$	8	A
	TO-220A(Ins)/ TO-220F(Ins) ( $T_c=95^\circ\text{C}$ )			
	TO-262 ( $T_c=90^\circ\text{C}$ )			
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$ )		$I_{TSM}$	80	A

I <sup>2</sup> t value for fusing (tp=10ms)	I <sup>2</sup> t	32	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2×I <sub>GT</sub> )	di/dt	50	A/μs
Peak gate current	I <sub>GM</sub>	4	A
Average gate power dissipation	P <sub>G(AV)</sub>	1	W
Peak gate power	P <sub>GM</sub>	5	W

**ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25°C unless otherwise specified)

**3 Quadrants**

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II - III	MAX	5	10	35	50	mA
V <sub>GT</sub>		I - II - III	MAX	1.5				V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	I - II - III	MIN	0.2				V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX	20	25	50	70	mA
		II		25	35	70	90	
I <sub>H</sub>	I <sub>TM</sub> =100mA		MAX	15	20	40	60	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C		MIN	50	200	500	1000	V/μs

**4 Quadrants**

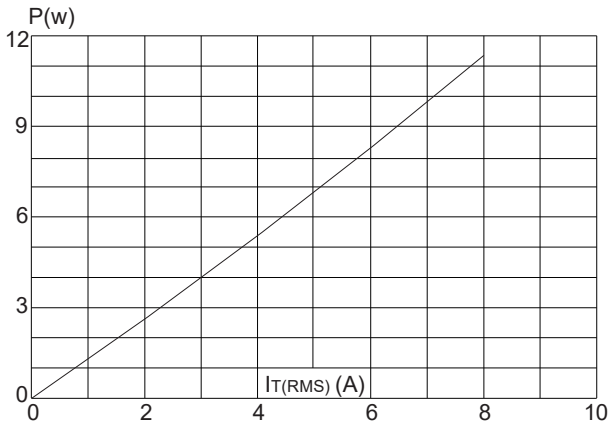
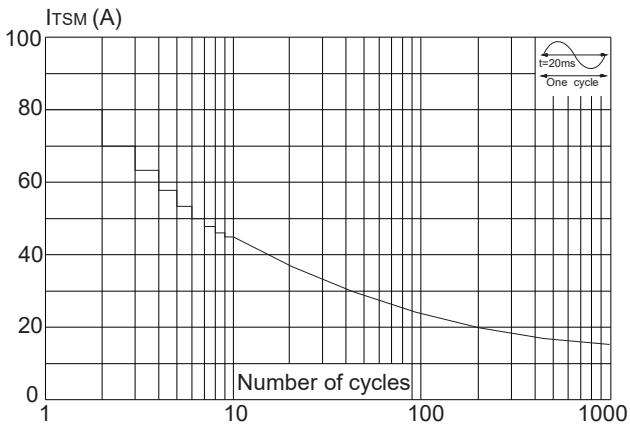
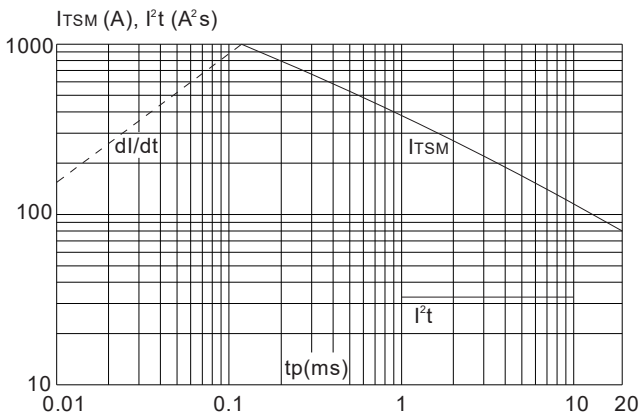
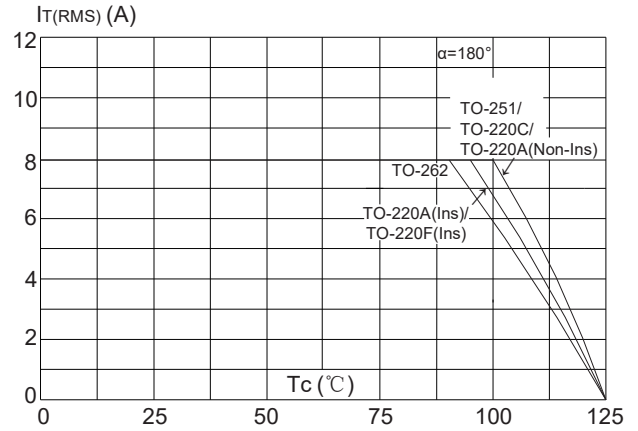
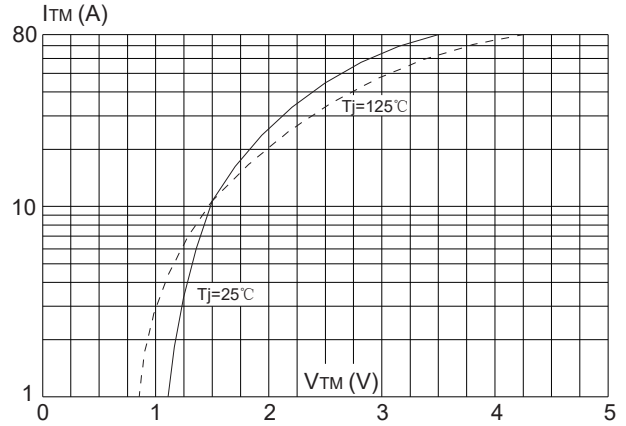
Symbol	Test Condition	Quadrant		Value		Unit
				C	B	
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II - III	MAX	25	50	mA
		IV		50	70	
V <sub>GT</sub>		ALL	MAX	1.5		V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	ALL	MIN	0.2		V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III - IV	MAX	50	70	mA
		II		70	90	
I <sub>H</sub>	I <sub>TM</sub> =200mA		MAX	40	60	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C		MIN	200	500	V/μs

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM} = 11A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	1.5	V
$I_{DRM}$	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$	5	$\mu A$
$I_{RRM}$		$T_j = 125^\circ C$	1	mA

**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251	2.1	$^\circ C/W$
		TO-220A(Ins)	2.7	
		TO-220C/ TO-220A(Non-Ins)	1.8	
		TO-220F(Ins)	2.9	
		TO-262	3.0	

**FIG.1:** Maximum power dissipation versus RMS on-state current

**FIG.3:** Surge peak on-state current versus number of cycles

**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )

**FIG.2:** RMS on-state current versus case temperature

**FIG.4:** On-state characteristics (maximum values)

**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature
